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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/519,699	
			Filed	September 14, 2005	
			First Named Inventor	Thomas N. Horsky et al.	
			Group Art Unit	2881	
			Examiner Name	John R. Lee	
Sheet	1	of	2	Attorney Docket Number	211843-00032

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. 1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code 2 (if known)			
	A1	6,013,546	01-11-2000	Gardner et al.	
	A2	2002/070672	06-13-2002	Horsky	
	A3	2007/0194252	08-23-2007	Horsky	
	A4	2007/0181830	08-09-2006	Horsky	

Examiner Initials*	Cite No. 1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code 3 - Number 4 - Kind Code 5 (if known)				
	B1	UK 1258125	12-22-1971	Ceskoslovenska Akademie		
	B2	EPO Search Report 03762087	01-17-2008			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher city and/or country where published	T ²
	C1	Goto et al. "Novel Shallow Junction Technology Using Decarborane (B10H14)" ELECTRON DEVICES MEETING, 1996., Int'l San Francisco, CA, USA 8-11 Dec. 1996, NY, NY, USA, IEEE, US, p. 435-438, XP010207579	
	C2	Ishikawa et al.: "Negative-Ion Implantation Technique" NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH, SECTION - B: BEAM INTERACTIONS WITH MATERIALS AND ATOMS, ELSEVIER,, Amsterdam, NL, vol. 96, No. 1/2, March 1995 (1995-03), Pages 7-12, XP004010949.	
	C3	Takeuchi et al. "Shallow Junction formation By Polyatomic Cluster Ion Implantation", Austin, TX, US 16-21 June 1996, NY, NY, USA, IEEE, US Page 772-775, XP010220650	